



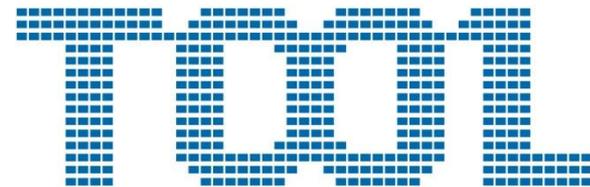
Beam
Initiative

eBeam Initiative Meeting

Solving the Impossible 80 Hour Mask Problem

Aki Fujimura
CEO – D2S, Inc.
Managing Sponsor – eBeam Initiative
BACUS Update – September 14, 2010

Welcome to New Members at BACUS



34 Member Companies & Advisors



Marty Deneroff
Consultant



Jack Harding
eSilicon



Colin Harris
PMC-Sierra



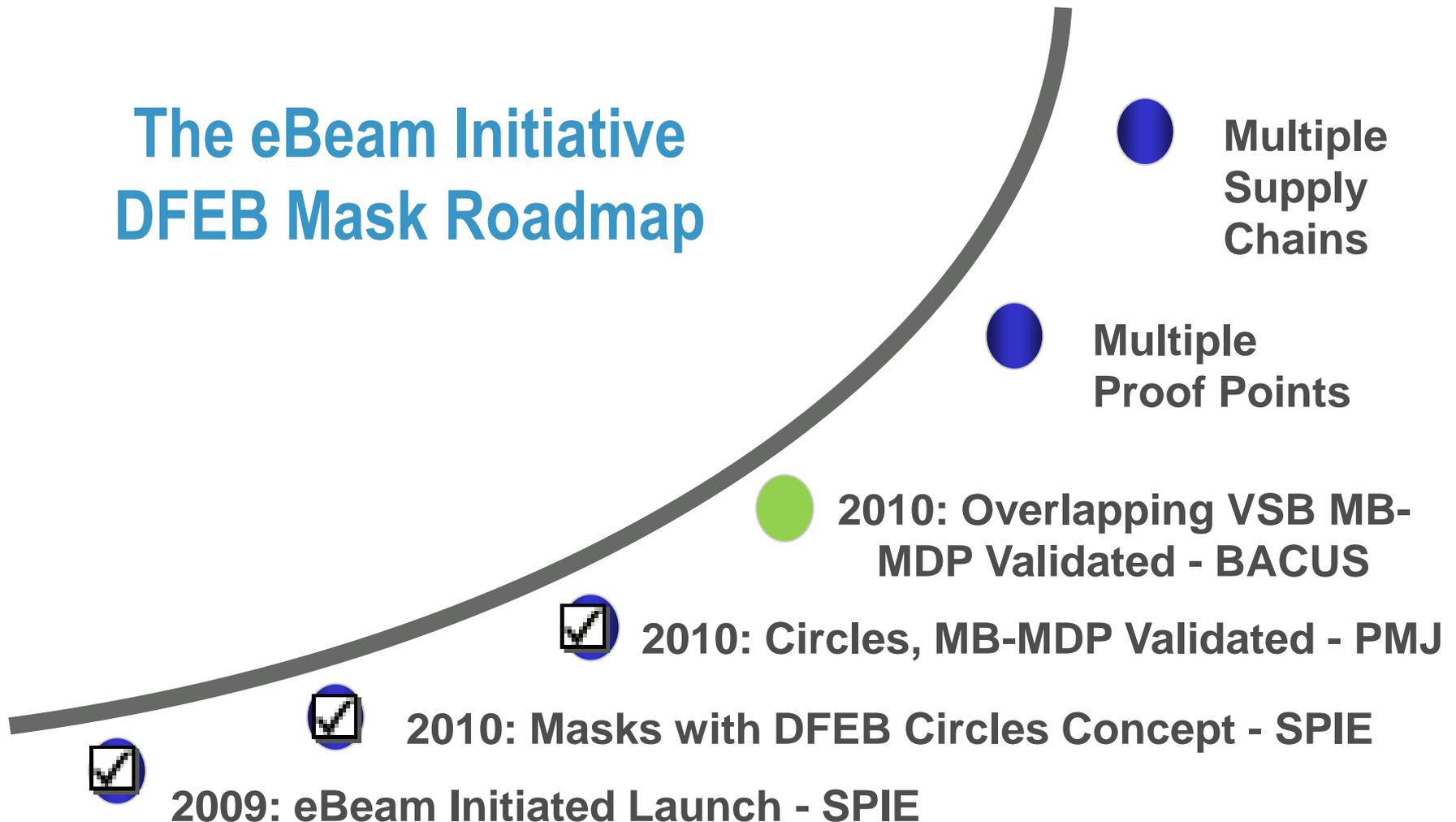
Riko Radojic
Qualcomm



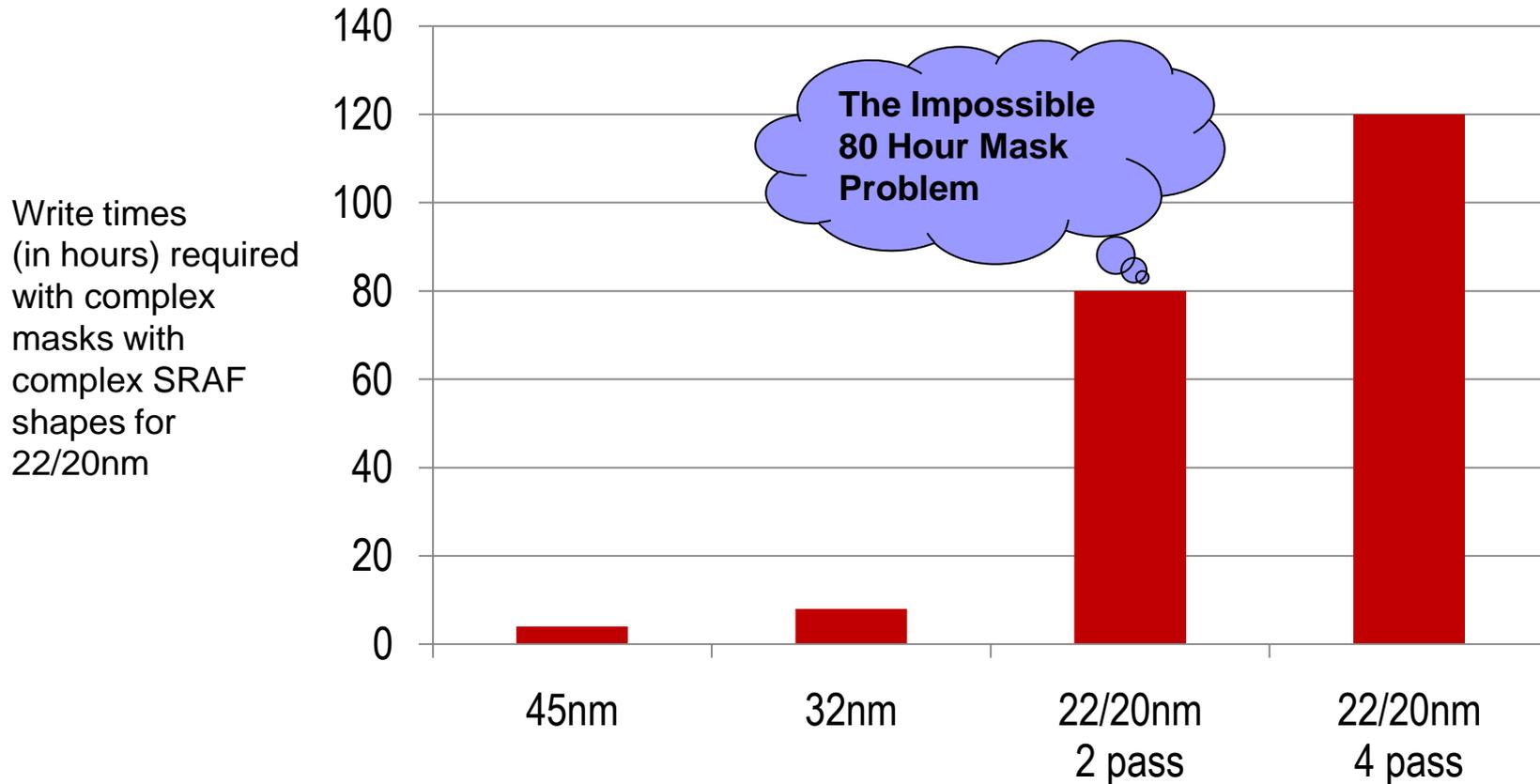
Jean-Pierre Geronimi
ST



The eBeam Initiative DFEB Mask Roadmap

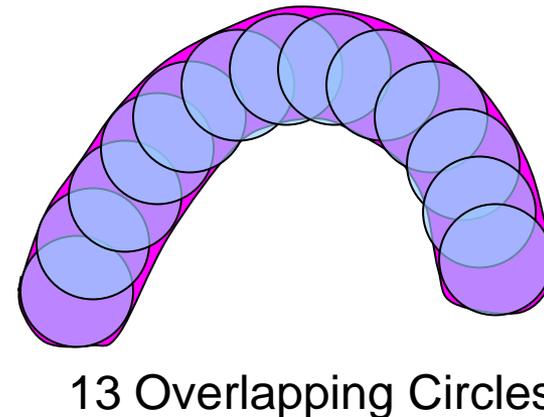
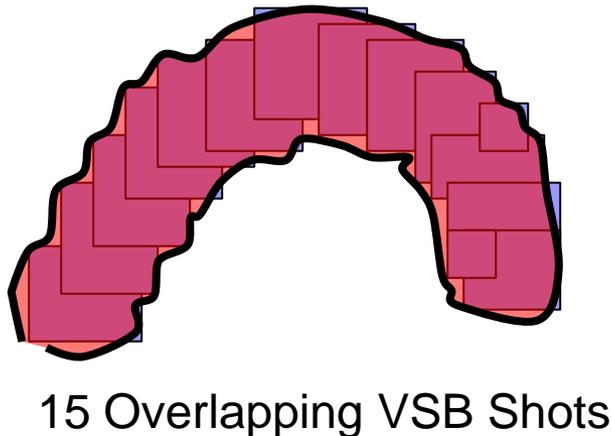
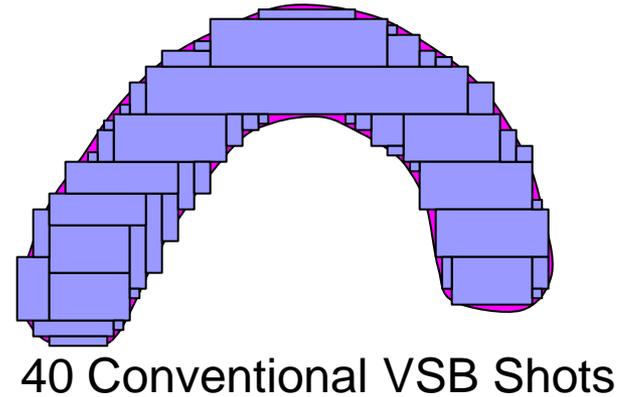
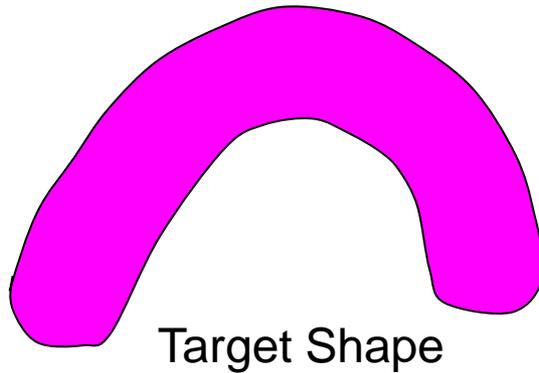


193i at 22/20nm Requires Complex Masks

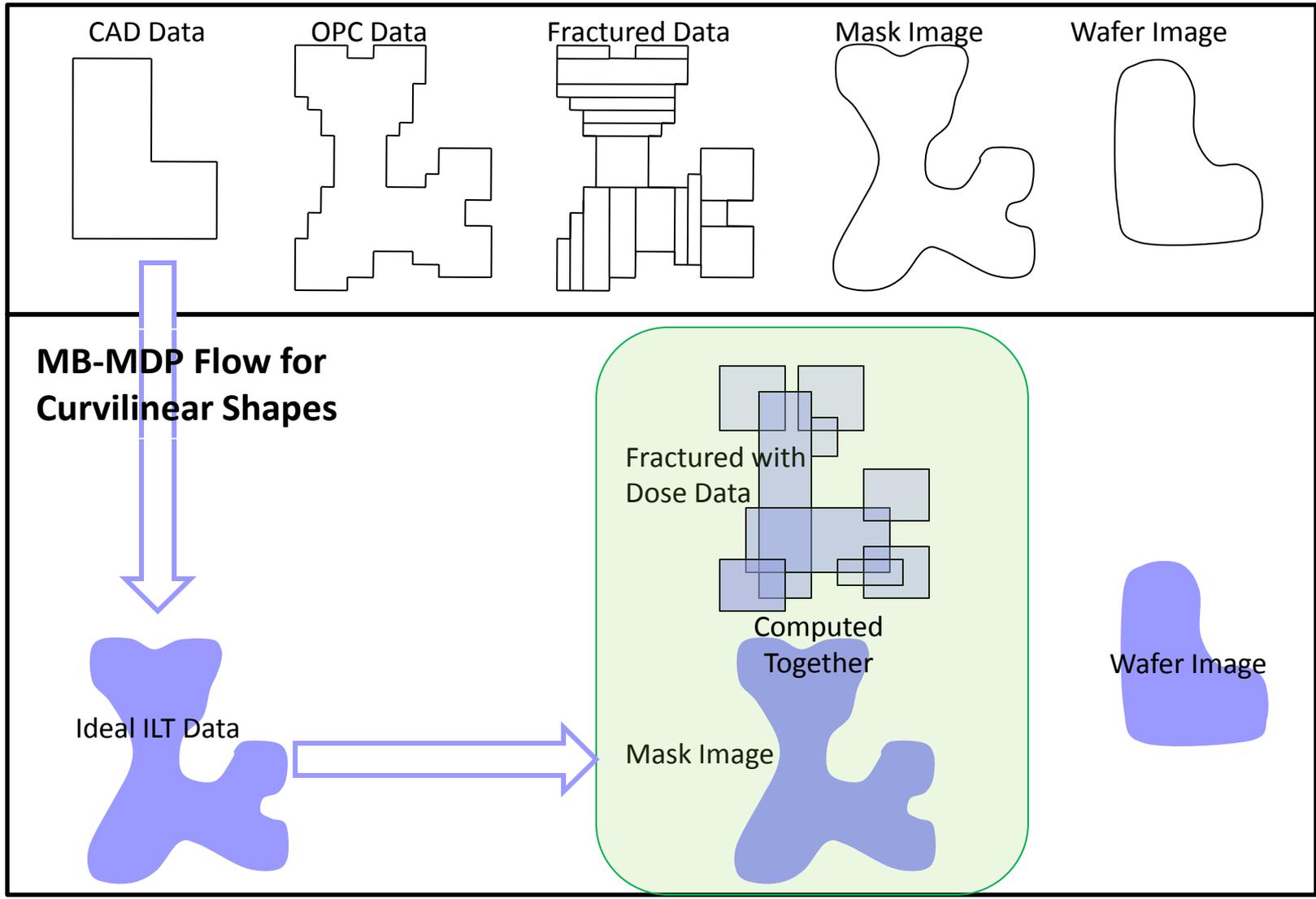


Source: D2S, Inc. projection of write times from shot counts projected in BACUS

DFEB Mask Addresses the 80 Hour Mask by Using Overlapping VSB and Circle Shots

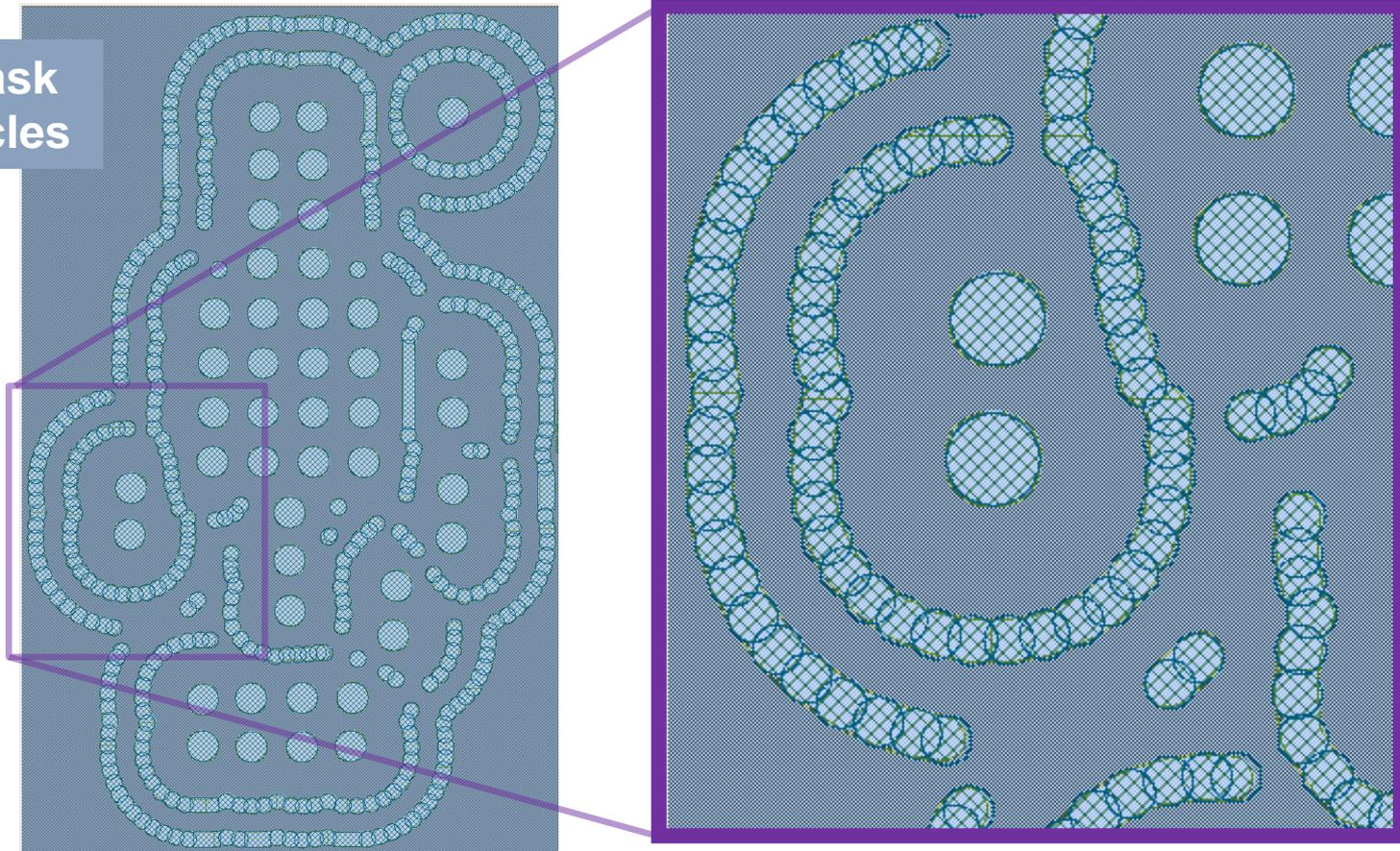


DFEB Mask Uses Model-based Mask Data Prep



PMJ 2010: First Proof of Circular Shots

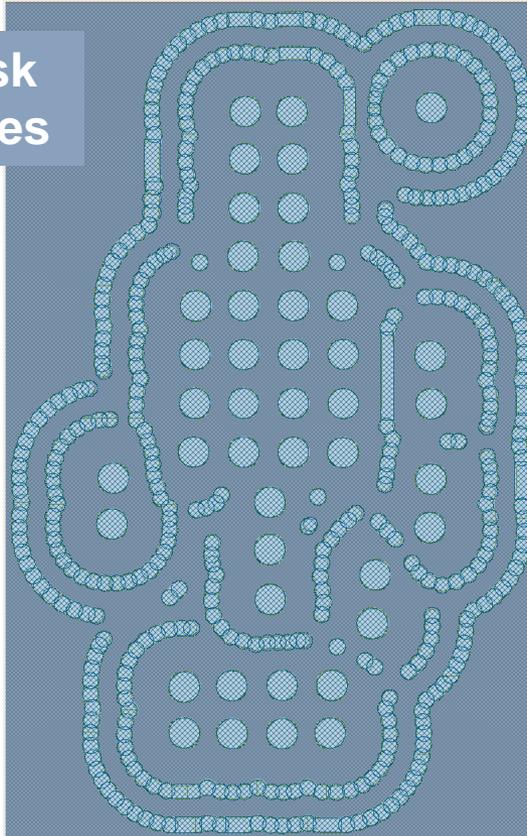
Ideal Mask
with Circles



PMJ 2010: JEOL & D2S

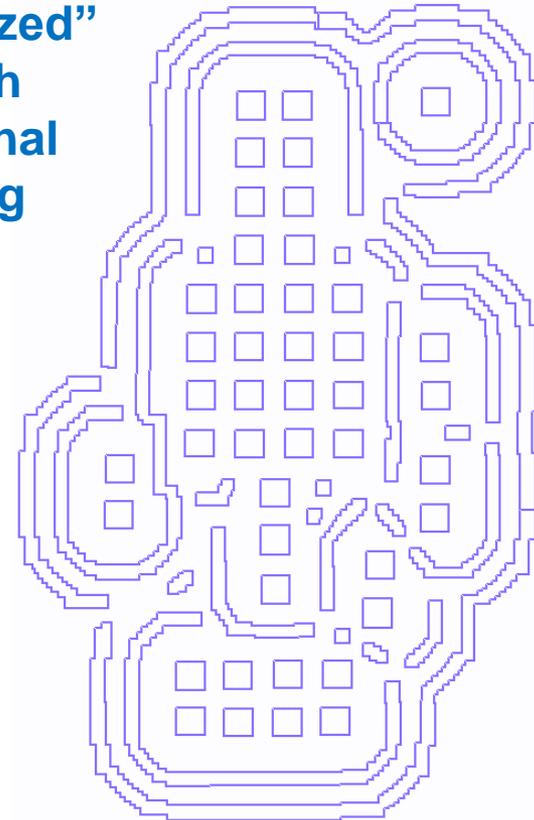
30% Shot Count Reduction

Ideal Mask
with Circles



484 (Circle + VSB) Shots
Better CDU with Circular Main Features

“Manhattanized”
Mask with
Conventional
Fracturing

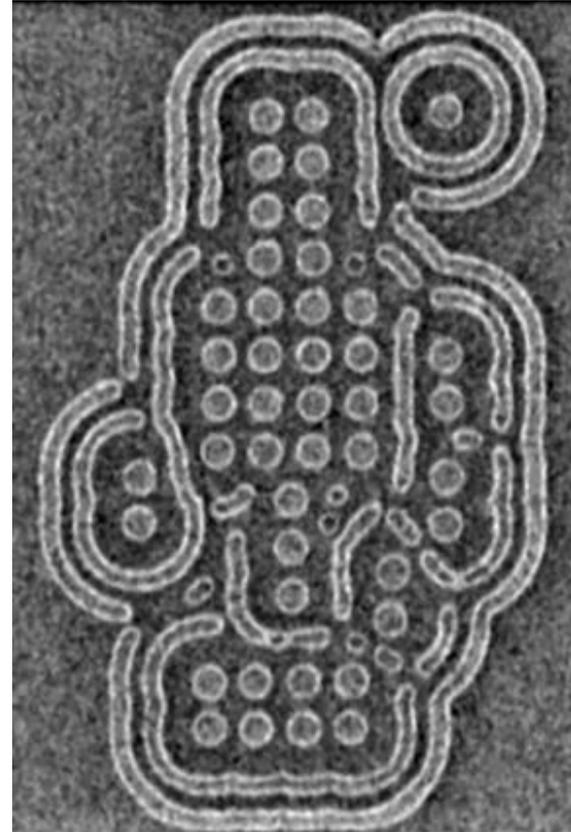
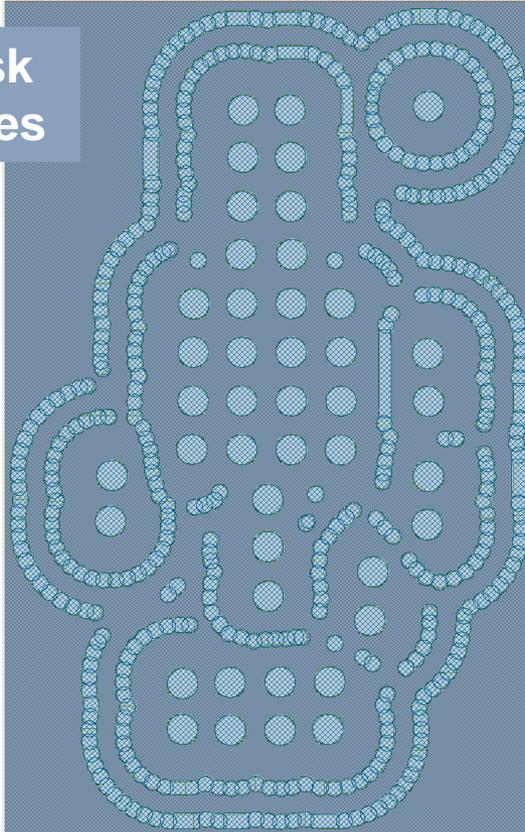


~620 conventional VSB shots

PMJ 2010: JEOL & D2S

Test Exposed with JBX-3200MV

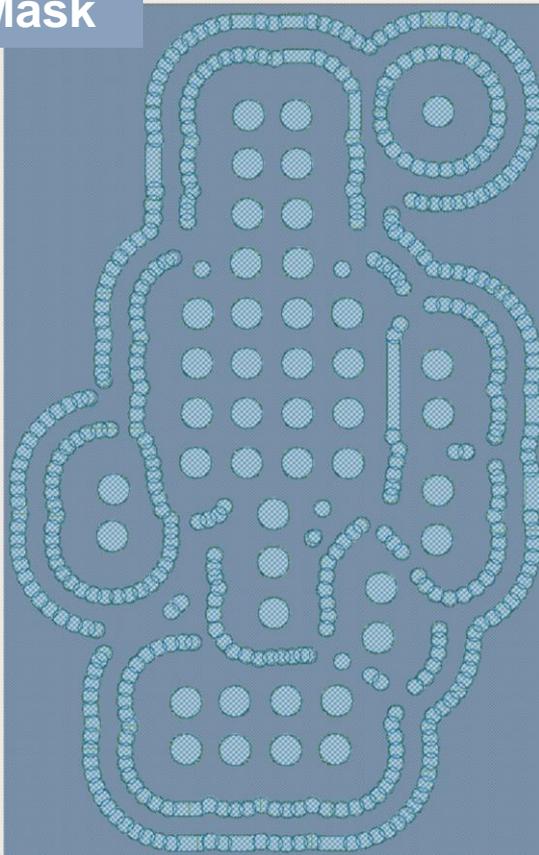
Ideal Mask
with Circles



CD-SEM of ideal ILT using DFEB Mask

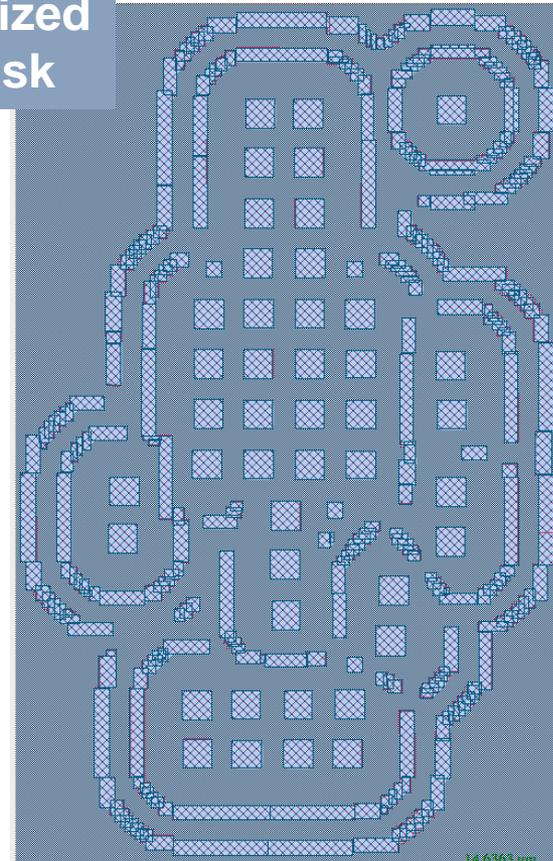
New for BACUS 2010: VSB-only solution

Ideal Mask



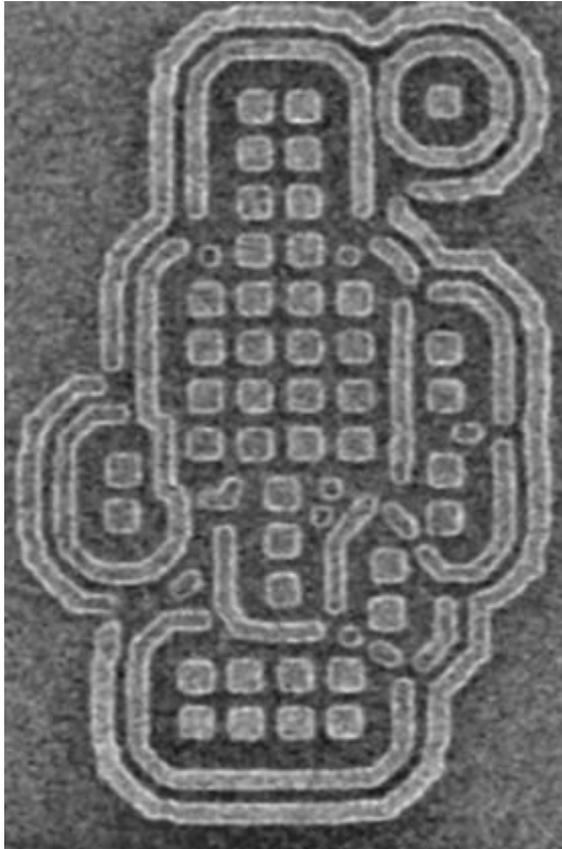
484 Circle + VSB Shots
Better CDU with Circular Main Features

D2S Optimized
DFEB Mask

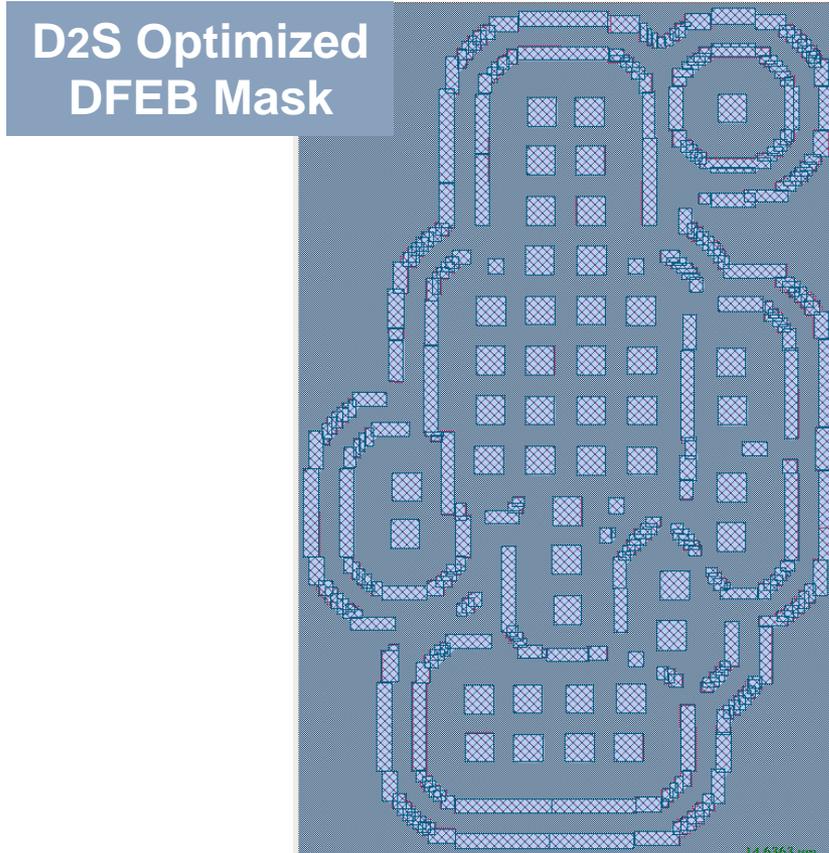


402 Overlapped VSB Shots (unassigned dose)
vs. ~620 conventional shots

DFEB Mask Improves Contacts: ILT with 9 VSB shots per contact

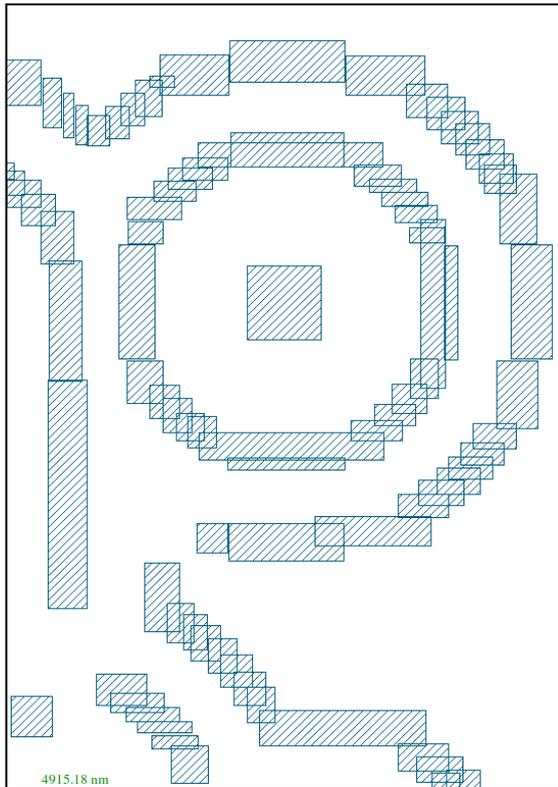


Test Printed on JEOL JBX 3200-MV



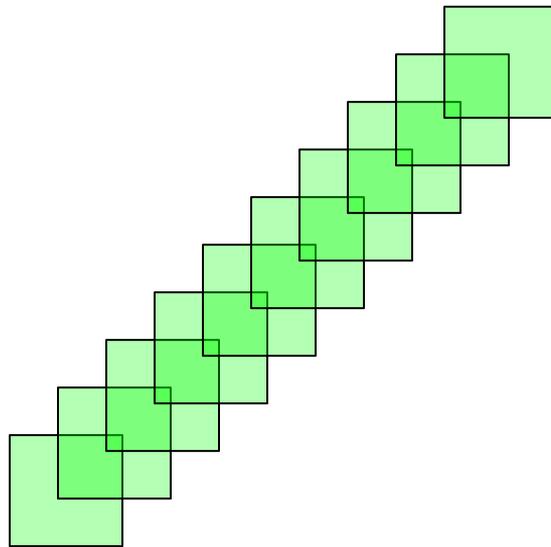
402 Overlapped VSB Shots (unassigned dose)
vs. ~620 conventional shots

Manhattanized ILT with DFEB Mask Using VSB-only MB-MDP



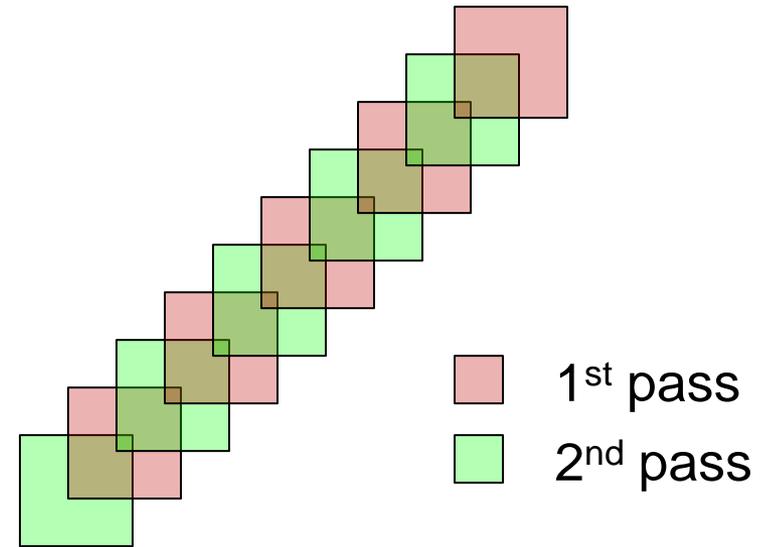
Zoomed in pictures of overlapped shots and the
CD-SEM of the printed mask

New for BACUS 2010: Further 25% reduction for SRAF writing



Before:

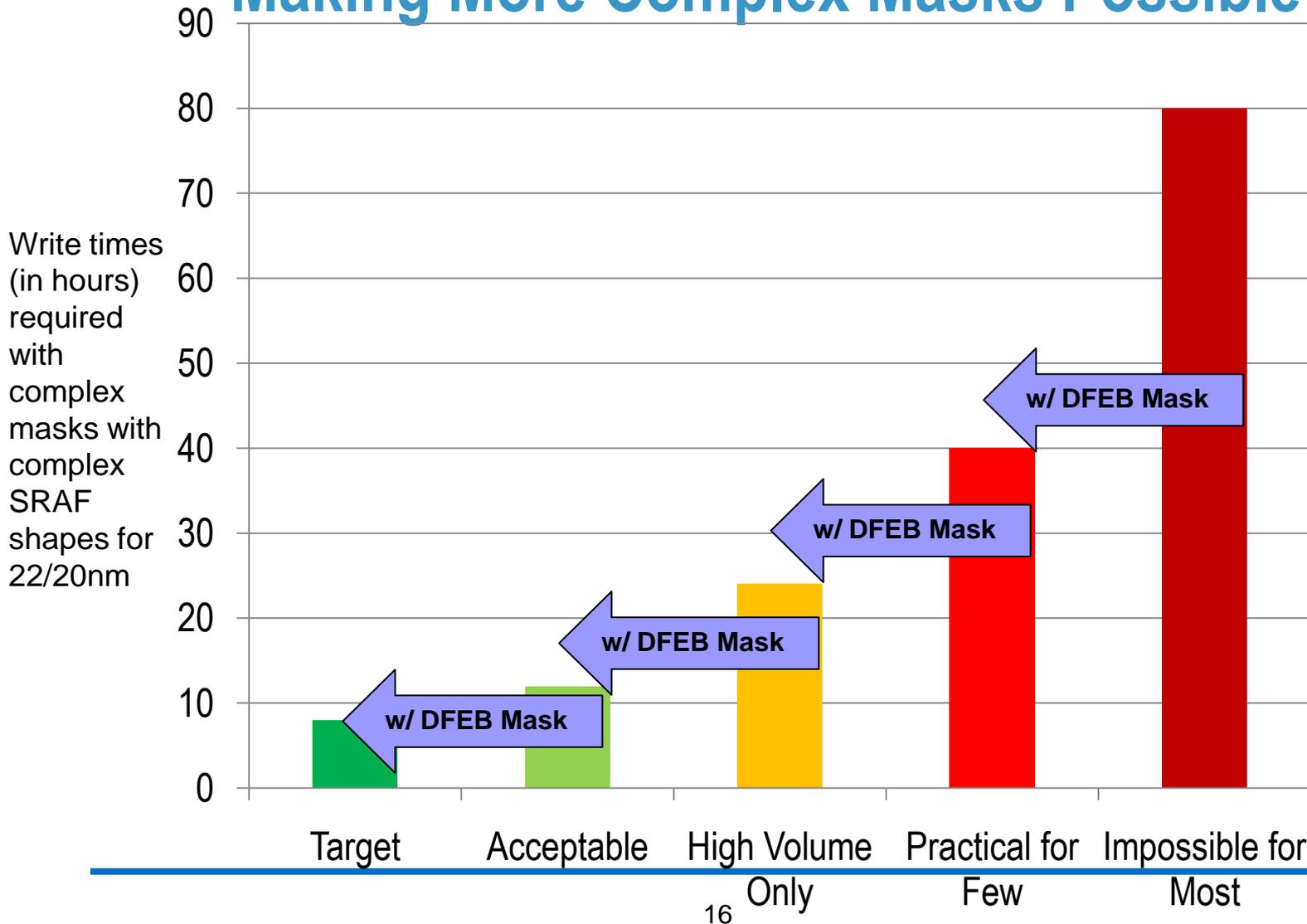
All shots with $\frac{1}{2}$ dose
in 2 passes or $\frac{1}{4}$
dose in 4 passes



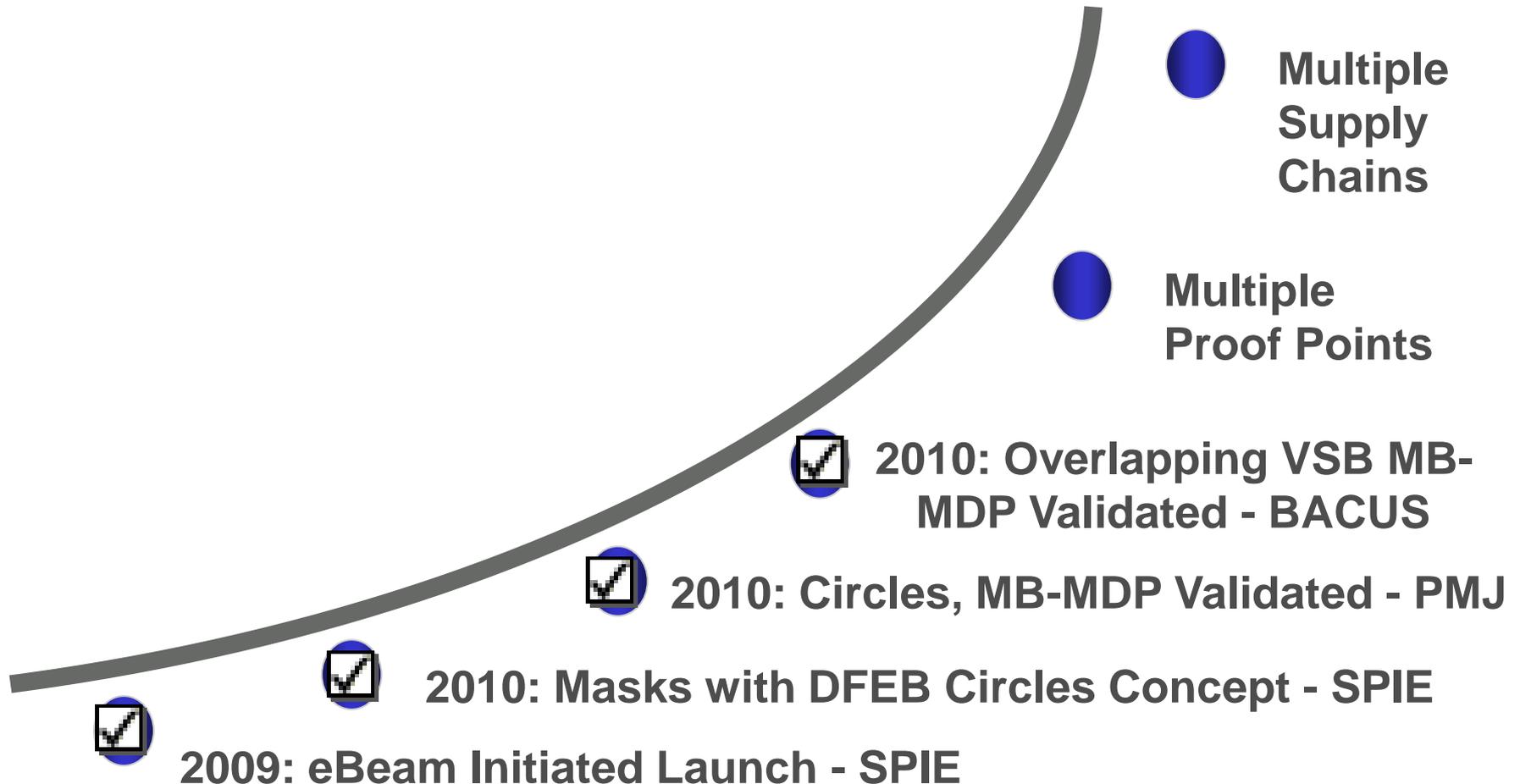
New:

Every other shot with full
dose per pass saves 50% of
blanking time
(Only for SRAF writing)

Summary: DFEB Mask Reduces Write Times Making More Complex Masks Possible



Summary: Steady Progress Towards Solving the “Impossible” 80 Hour Mask



Thanks to Members for BACUS Papers

- **September 14**

- Session 2: Pattern Generation - Improvement of Mask Write Time for Curvilinear Assist Features at 22nm
- Session 6: Mask Data Preparation - Writing 32nm-hp Contacts with Curvilinear Assist Features
- Session 8: Optical Proximity Correction - Impact of Model-Based Fracturing on Proximity Effect Correction Methodology

- **September 15**

- 8:00am, Steinbeck Forum – Special Session on E-Beam Direct Write



Beam
Initiative